

Taiwan Semiconductor

# PerF∃T<sup>™</sup> Power Transistor

#### **FEATURES**

- Ultra-low On-resistance
- Wettable Flank leads for Enhanced AOI
- 100% UIS and Rg tested
- 175°C Operating Junction Temperature
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
V	DS	40	V	
5 / \	$V_{GS} = 10V$	1.9	0	
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	2.7	mΩ	
$Q_g$	$V_{GS} = 4.5V$	49	nC	



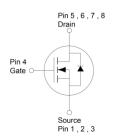




#### **APPLICATIONS**

- DC-DC Converters
- · Solenoid and Motor Drivers
- Load Switch





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	±16	V
Continuous Drain Current, Silicon limited	$T_C = 25^{\circ}C$	I <sub>D</sub>	216	Α
	$T_C = 25^{\circ}C$		100	
Continuous Drain Current (Note 1)	$T_C = 100$ °C	$I_{D}$	100	А
	$T_A = 25^{\circ}C$		30	
Pulsed Drain Current		I <sub>DM</sub>	400	Α
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	42.8	А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	274.5	mJ
Total Dower Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	150	W
Total Power Dissipation	$T_C = 125$ °C		50	VV
Operating Junction and Storage Temperature Range		$T_J,T_STG$	- 55 to +175	°C

THERMAL RESISTANCE				
PARAMETER	SYMBOL	MAXIMUM	UNIT	
Thermal Resistance – Junction to Case	$R_{\Theta JC}$	1	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	50	°C/W	

**Note**:  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JC}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

1

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 1mA$	BV <sub>DSS</sub>	40			٧
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.4	1.8	2.2	V
Gate-Source Leakage Current	$V_{GS} = \pm 16V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
	$V_{GS} = 0V, V_{DS} = 40V$				1	
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$ $T_{J} = 125^{\circ}C$	I <sub>DSS</sub>			100	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 50A$	_		1.3	1.9	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 50A$	R <sub>DS(on)</sub>		1.6	2.7	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 25A$	g <sub>fs</sub>		130.7		S
Dynamic						
Total Gate Charge	$V_{GS} = 4.5V, V_{DS} = 25V,$ $I_{D} = 30A$	$Q_g$		49		
Total Gate Charge		$Q_g$		104		nC
Gate-Source Charge	$V_{GS} = 10V, V_{DS} = 25V,$	$Q_{gs}$		19		
Gate-Drain Charge	$I_D = 30A$	$Q_gd$		15		
Input Capacitance		C <sub>iss</sub>		6282		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$	C <sub>oss</sub>		1204		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		63		
Gate Resistance	f = 1.0MHz	$R_g$		1.0		Ω
Switching (Note 4)						
Turn-On Delay Time		t <sub>d(on)</sub>		16		
Rise Time	$V_{GS} = 10V, V_{DS} = 25V,$	t <sub>r</sub>		77		
Turn-Off Delay Time	$I_D = 30A, R_G = 3.3\Omega$	t <sub>d(off)</sub>		74		nS
Fall Time		t <sub>f</sub>		104		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 50A$	$V_{SD}$			1.1	V
Reverse Recovery Time	I <sub>S</sub> = 30A,	t <sub>rr</sub>		61		nS
Reverse Recovery Charge	di/dt = 100A/µs	Q <sub>rr</sub>		97		nC

### Notes:

- 1. Package current limit.
- 2. L = 0.3mH,  $V_{GS} = 10V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$ .
- 3. Pulse test: Pulse Width  $\leq$  300µs, duty cycle  $\leq$  2%.
- 4. Switching time is essentially independent of operating temperature.

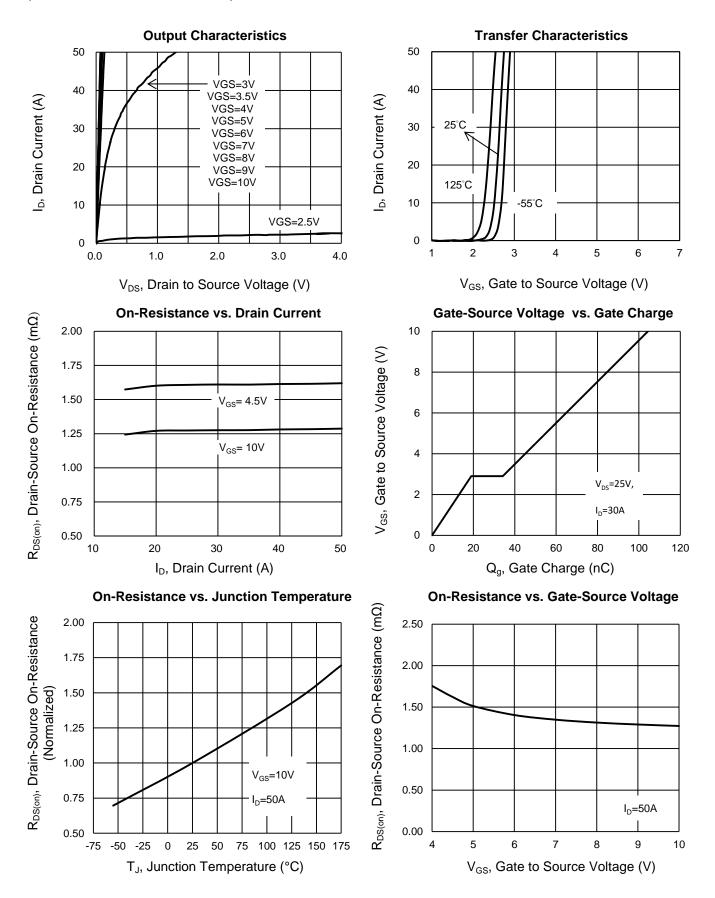
### **ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM019NH04LCR RLG	PDFN56U	2,500pcs / 13" Reel



# **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)



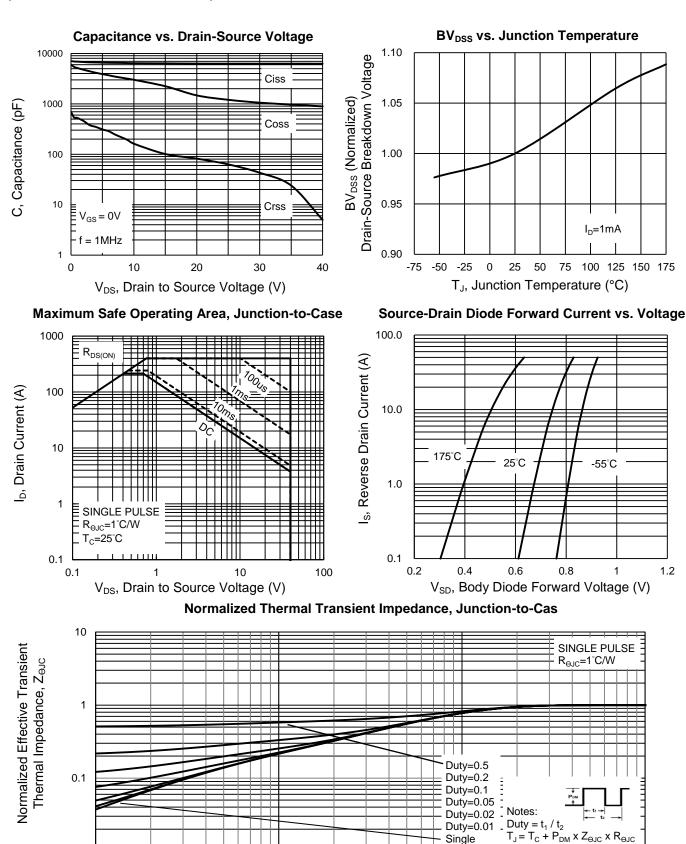
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0.0001

#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



t, Square Wave Pulse Duration (sec)

0.001

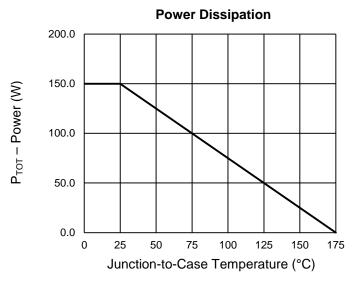
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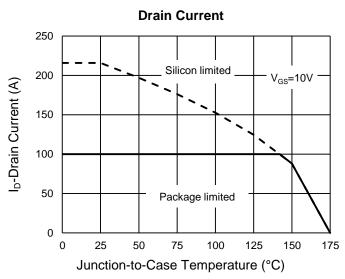
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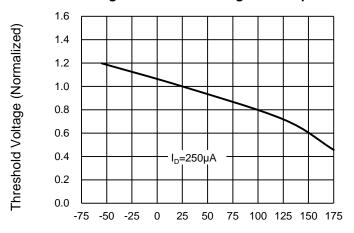
### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)





### Normalized gate threshold voltage vs Temperature



T<sub>J</sub>, Junction Temperature (°C)

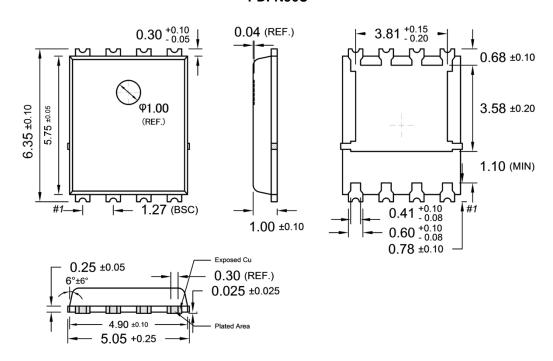
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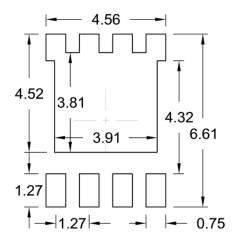


### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

#### PDFN56U



# **SUGGESTED PAD LAYOUT** (Unit: Millimeters)



6

## **MARKING DIAGRAM**



Y = Year Code

**WW** = Week Code (01~52)

 $\mathbf{L} = \text{Lot Code } (1 \sim 9, A \sim Z)$ 

**F** = Factory Code



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